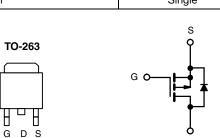


Top View

Vishay Siliconix

Automotive P-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.040				
$R_{DS(on)}$ (Ω) at V_{GS} = - 4.5 V	0.048				
I _D (A)	- 40				
Configuration	Single				



FEATURES

- TrenchFET® Power MOSFET
- · Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM40P10-40L-GE3

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	- 100	M		
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	l _D	- 40		
Continuous Drain Current	T _C = 125 °C		- 23		
Continuous Source Current (Diode Conduction	I _S	- 60	Α		
Pulsed Drain Current ^b		I _{DM}		- 160	
Single Pulse Avalanche Current	lanche Current		- 45		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	100	mJ	
Marrian Danier Diaginations	T _C = 25 °C	D.	150	W	
Maximum Power Dissipation ^b	T _C = 125 °C	- P _D	50	Į vv	
Operating Junction and Storage Temperature	e Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient F	PCB Mount ^c	R _{thJA}	40	°C/M		
Junction-to-Case (Drain)		R _{thJC}	1	°C/W		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•		,	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 100	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		- 2.0	- 2.5	ľ	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = - 100 V	1	-	- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 100 V, T _J = 125 °C	-	-	- 50	μA	
		V _{GS} = 0 V	V _{DS} = - 100 V, T _J = 175 °C	=	-	- 250	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 30	-	-	Α	
		V _{GS} = - 10 V	I _D = - 17 A	=	0.033	0.040	Ω	
Drain-Source On-State Resistance ^a	В	V _{GS} = - 10 V	I _D = - 17 A, T _J = 125 °C	-	-	0.060		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 17 A, T _J = 175 °C	=.	-	0.099		
		V _{GS} = - 4.5 V	I _D = - 14 A	=	0.0367	0.0480		
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		=.	47	-	S	
Dynamic ^b	•							
Input Capacitance	C _{iss}				4236	5295		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 25 V, f = 1 MHz	=	314	395	pF	
Reverse Transfer Capacitance	C _{rss}			=.	216	270		
Total Gate Charge ^c	Qg			=.	89	134	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -50 \text{ V}, I_{D} = -40 \text{ A}$	=	11.6	-		
Gate-Drain Charge ^c	Q _{gd}			=.	19.6			
Gate Resistance	R _g		f = 1 MHz		2.89	4.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}				10	15		
Rise Time ^c	t _r	V_{DD} = - 50 V, R_L = 1.25 Ω I_D \cong - 40 A, V_{GEN} = - 10 V, R_g = 1 Ω		=.	10	15	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	63	95		
Fall Time ^c	t _f			-	20	30		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 160	Α	
Forward Voltage	V_{SD}	I _F = - 30 A, V _{GS} = 0 V		_	- 0.9	- 1.5	V	

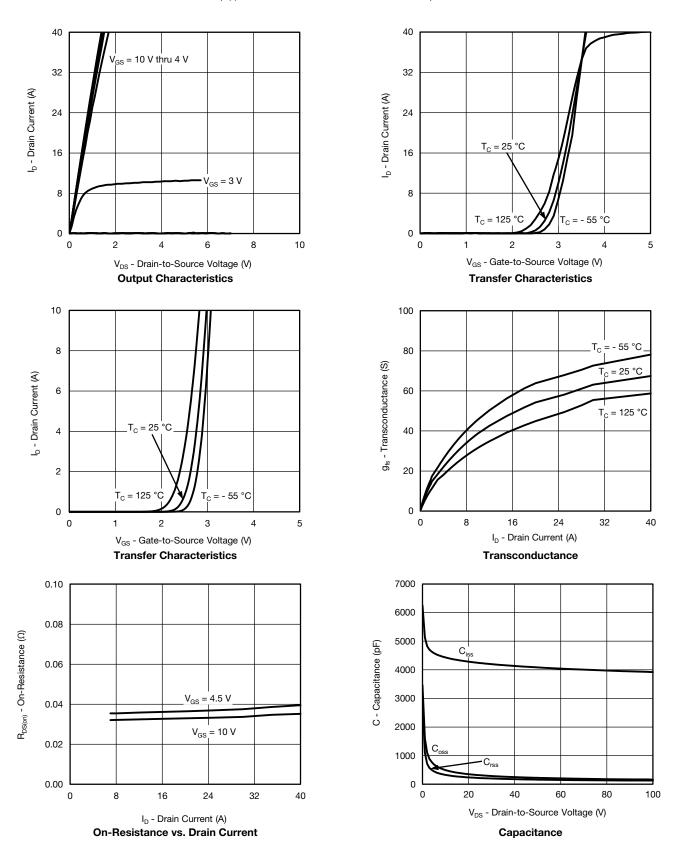
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

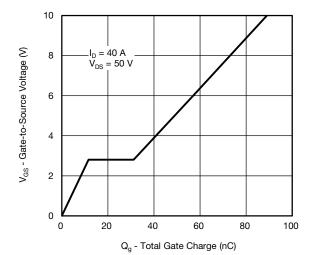


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

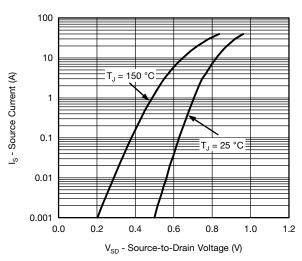




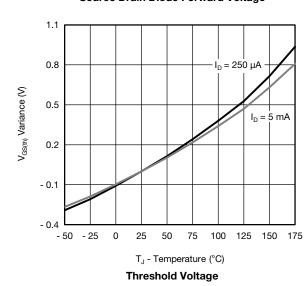
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

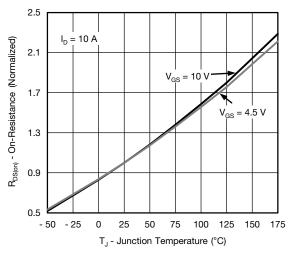


Gate Charge

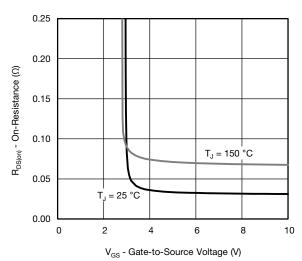


Source Drain Diode Forward Voltage

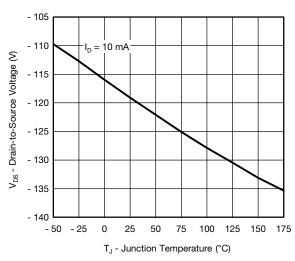




On-Resistance vs. Junction Temperature



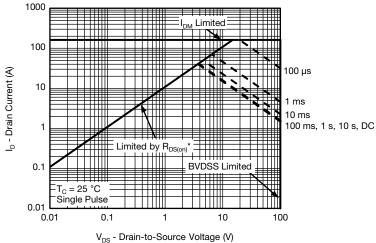
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

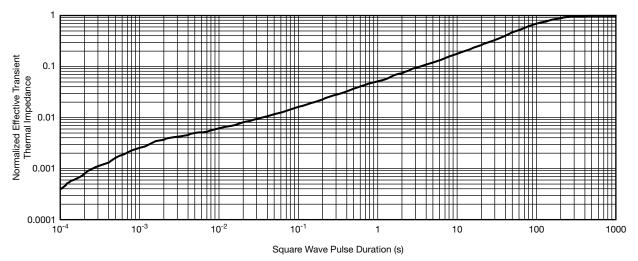


THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



 v_{DS} - Drain-to-Source voltage (v) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

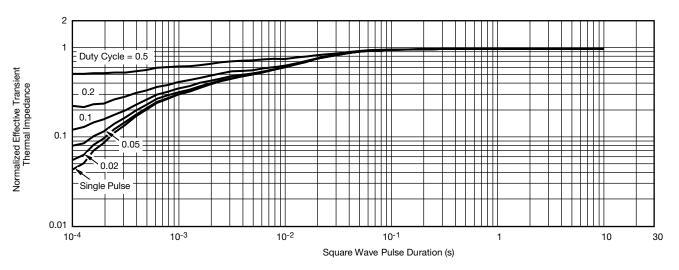
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

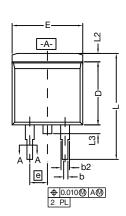
Note

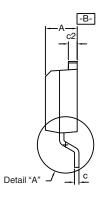
- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

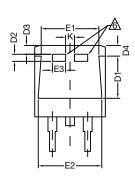
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67053.



TO-263 (D²PAK): 3-LEAD

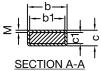








DETAIL A (ROTATED 90°)



_ - b1 , , ,	
≥ 	- -

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

	INCHES		HES	MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1 0.220		0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	.355 0.375 9.017 9.52		9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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